

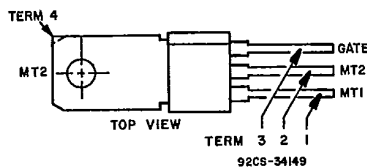
2.5-A Sensitive-Gate Silicon Triacs

For AC Power Switching

Features:

- 800V, 125 Deg. C T_J Operating
- High dv/dt and di/dt Capability
- Low Switching Losses
- High Pulse Current Capability
- Low Forward and Reverse Leakage
- Sipos Oxide Glass Multilayer Passivation System
- Advanced Unisurface Construction
- Precise Ion Implanted Diffusion Source

TERMINAL DESIGNATIONS



JEDEC TO-202AB

The RCA-T2320, T2322, T2323 and T2327, series triacs are gate-controlled full-wave silicon ac switches that are designed to switch from an off-state to an on-state for either polarity of applied voltage with positive or negative gate triggering voltages. The gate sensitivity of these triacs permits the use of economical transistorized or integrated cir-

cuit control circuits and enhances their use in low-power phase-control and load-switching applications.

All types in each series utilize the JEDEC-TO-202AB (VER-SATAB) plastic package.

MAXIMUM RATINGS, Absolute-Maximum Values:

	3mA Gate	T2320A	T2320B	T2320D	T2320E	T2320M	T2320N	
	10 mA Gate	T2322A	T2322B	T2322D	T2322E	T2322M	T2322N	
	25 mA Gate	T2323A	T2323B	T2323D	T2323E	T2323M	T2323N	
	5 mA Gate	T2327A	T2327B	T2327D	T2327E	T2327M	T2327N	
V_{DROM}^{Δ} (Gate Open, $T_J = -40$ to 125°C)		100	200	400	500	600	800	
$I_{T(RMS)}$ ($T_C = 95^{\circ}\text{C}$)				2.5				A
$I_{T(RMS)}$ ($T_A = 25^{\circ}\text{C}$)				1				A
I_{TSM} (for 1 full cycle)				25				A
di/dt :				100				A/ μs
I^2t [At T_C shown for $I_{T(RMS)}$] (Half-sine wave):								
$t = 20$ ms				3.4				A ^2s
$= 2.5$ ms				1.7				A ^2s
$= 0.5$ ms				1				A ^2s
For other time values				See Fig. 5				
I_{GTM}^{Δ} (For 1 μs max.)				1				A
P_{GM} (for 1 μs max.)				10				W
$P_{G(AV)}$ (Averaging time 10ms max.)				0.1				W
T Storage				-40 to 150				$^{\circ}\text{C}$
T_J				-40 to 125				$^{\circ}\text{C}$
T_J^{Δ} :								
During soldering for 10 s maximum at distance								
$\geq 1/16$ in. (1.58 mm) from seating plane				225				$^{\circ}\text{C}$

Δ For either polarity of main terminal 2 voltage (V_{MT2}) with reference to main terminal 1.

Δ For either polarity of gate voltage (V_G) with reference to main terminal 1.

Δ For temperature measurement reference point, see *Dimensional Outlines*.

ELECTRICAL CHARACTERISTICS

At Maximum Ratings Unless Otherwise Specified, and at Indicated Case Temperature (T_C)

▲ For either polarity of main terminal 2 voltage (V_{MT2}) with reference to main terminal 1.
● For either polarity of gate voltage (V_G) with reference to main terminal 1.

▲ For either polarity of main terminal 2 voltage (V_{MT2}) with reference to main terminal 1.
● For either polarity of gate voltage (V_G) with reference to main terminal 1.

T2320, T2322, T2323, T2327 Series

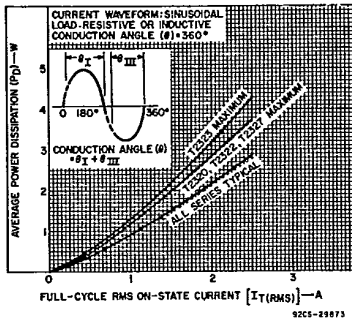


Fig. 1 — Power dissipation as a function of on-state current.

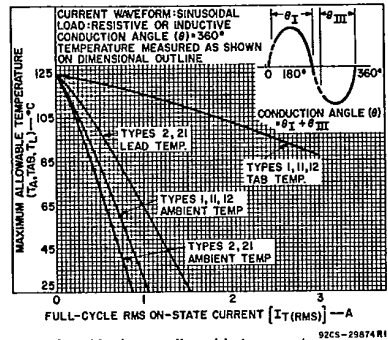


Fig. 2 — Maximum allowable temperature as a function of on-state current for T2320, T2322, and T2327.

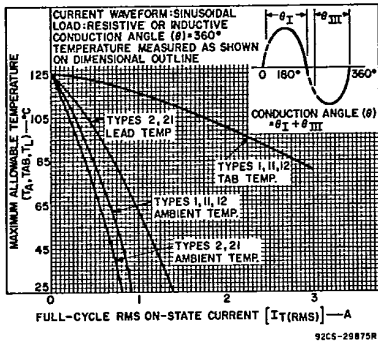


Fig. 3 — Maximum allowable temperature as function of on-state current for T2323.

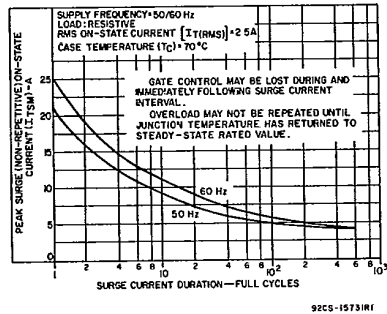


Fig. 4 — Peak surge on-state current as a function of surge-current duration.

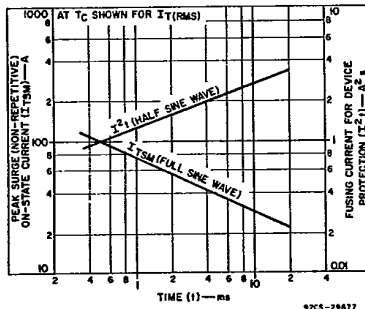


Fig. 5 — Peak surge on-state current and fusing current as a function of time.

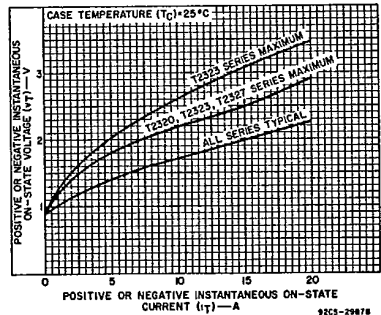


Fig. 6 — On-state current vs. on-state voltage.

T2320, T2322, T2323, T2327 Series

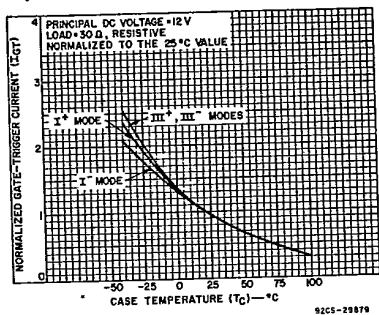


Fig. 7 — Gate-trigger current vs. case temperature.

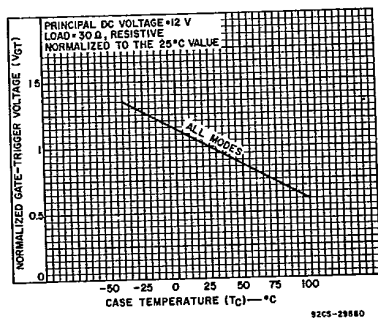


Fig. 8 — Gate-trigger voltage vs. case temperature.

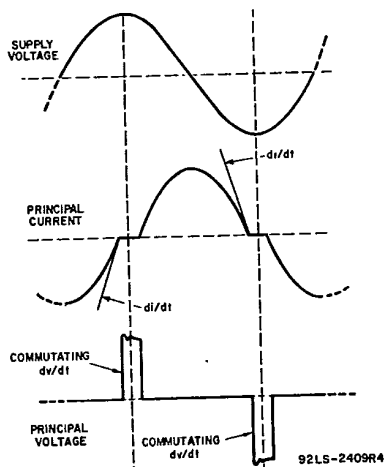


Fig. 10 — Relationship between supply voltage and principal current (inductive load) showing reference points for definition of commutating voltage (dv/dt).

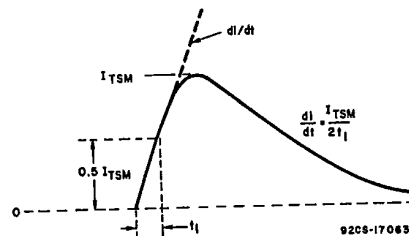
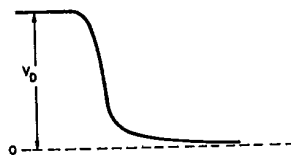


Fig. 9 — Rate-of-change of on-state current with time (defining di/dt).

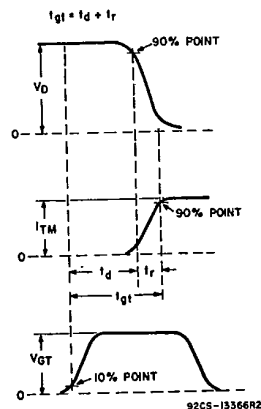


Fig. 11 — Relationship between off-state voltage, on-state current, and gate-trigger voltage showing reference points for definition of turn-on time (t_{gt}).